

**IN THE CLAIMS**

1. (canceled)

~~17~~ 2. (previously presented): The semiconductor apparatus according to claim 32, wherein said first-conductivity-type MOS output transistor and said first-conductivity-type MOS protection transistor are of an SOI structure.

~~18~~ 3. (currently amended): The semiconductor apparatus according to claim ~~2~~<sup>17</sup>, comprising:

[[a]] wherein the second-conductivity-type  $\pm$  area is connected to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor, and

wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type  $\pm$  area to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

4. (canceled)

~~19~~ 5. (previously presented): The semiconductor apparatus according to claim ~~32~~<sup>16</sup>, wherein the drain electrode of said first-conductivity-type MOS protection transistor is formed closer to the output electrode than the drain electrode of said first-conductivity-type MOS output transistor.

~~20~~ 6. (previously presented): The semiconductor apparatus according to claim ~~32~~<sup>16</sup>, wherein said first-conductivity-type MOS protection transistor is higher in electrostatic destruction withstanding voltage than said first-conductivity-type MOS output transistor.

~~21~~ 7. (original): The semiconductor apparatus according to claim ~~6~~<sup>20</sup>, wherein said first-conductivity-type MOS output transistor and said first-conductivity-type MOS protection transistor are of an SOI structure.

22/  
8. (currently amended): The semiconductor apparatus according to claim ~~7~~<sup>21</sup>, comprising:

[[a]] wherein the second-conductivity-type  $\pm$  area is connected to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor,

wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type  $\pm$  area to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

23/  
9. (previously presented): The semiconductor apparatus according to claim ~~8~~<sup>20</sup>, wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected by an electrode wiring to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

24/  
10. (previously presented): The semiconductor apparatus according to claim ~~9~~<sup>20</sup>, wherein the drain electrode of said first-conductivity-type MOS protection transistor is formed closer to the output electrode than the drain electrode of said first-conductivity-type MOS output transistor.

25/  
11. (original): The semiconductor apparatus according to claim 10, wherein said first-conductivity-type MOS output transistor and said first-conductivity-type MOS protection transistor are of an SOI structure.

26/  
12. (currently amended): The semiconductor apparatus according to claim ~~11~~<sup>25</sup>, comprising:

[[a]] wherein the second-conductivity-type  $\pm$  area is connected to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor,

wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type  $\pm$  area to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

~~27~~ 13. (previously presented): The semiconductor apparatus according to claim ~~10~~<sup>24</sup>, wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected by an electrode wiring to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

~~28~~ 14. (original): The semiconductor apparatus according to claim ~~13~~<sup>27</sup>, wherein said first-conductivity-type MOS output transistor and said first-conductivity-type MOS protection transistor are of an SOI structure.

~~29~~ 15. (currently amended): The semiconductor apparatus according to claim ~~14~~<sup>28</sup>, comprising:  
[[a]] wherein the second-conductivity-type  $\pm$  area is connected to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor,

wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type  $\pm$  area to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

~~1~~ 16. (currently amended): A semiconductor apparatus which protects a first-conductivity-type MOS output transistor and a second-conductivity-type MOS output transistor against a surge entering through an output electrode connected to each of drains of said first-conductivity-type MOS output transistor whose source is connected to ground and said second-conductivity-type MOS output transistor whose source is connected to a power supply, said apparatus comprising:

a first-conductivity-type MOS protection transistor having a drain connected to the drain of said first-conductivity-type MOS output transistor, a source connected to a source of said first-conductivity-type MOS output transistor, and a gate connected to a second-conductivity-type layer under a gate of said first-conductivity-type MOS output transistor; and

a second-conductivity-type MOS protection transistor having a drain connected to the drain of said second-conductivity-type MOS output transistor, a source connected to a source of said second-conductivity-type MOS output transistor, and a gate connected to a first-conductivity-type layer under a gate of said second-conductivity-type MOS output transistor;

wherein said first-conductivity-type MOS output transistor further includes a second-conductivity-type + area which is formed in said second-conductivity-type layer and substantially surrounds said drain electrode and said source electrode.

<sup>2</sup> ~~17~~. (original): The semiconductor apparatus according to claim ~~16~~<sup>1</sup>, wherein said first-conductivity-type MOS output transistor, said first-conductivity-type MOS protection transistor, said second-conductivity-type MOS output transistor, and said second-conductivity-type MOS protection transistor are of an SOI structure.

<sup>3</sup> ~~18~~. (currently amended): The semiconductor apparatus according to claim ~~17~~<sup>2</sup>, comprising:

[[a]] wherein the second-conductivity-type + area is connected to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor; and comprising

a first-conductivity-type area connected to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor,

wherein the gate of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type + area to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor, and

wherein the gate of said second-conductivity-type MOS protection transistor is connected via said first-conductivity-type area to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~4~~ 19. (original): The semiconductor apparatus according to claim ~~16~~, wherein the gates of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are connected by electrode wirings respectively to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor and to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~5~~ 20. (original): The semiconductor apparatus according to claim ~~16~~, wherein the drains of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are formed closer to the output electrode than the drains of said first-conductivity-type MOS output transistor and said second-conductivity-type MOS output transistor.

~~6~~ 21. (original): The semiconductor apparatus according to claim ~~16~~, wherein said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are higher in electrostatic destruction withstand voltage than said first-conductivity-type MOS output transistor and said second-conductivity-type MOS output transistor.

~~7~~ 22. (original): The semiconductor apparatus according to claim ~~21~~, wherein said first-conductivity-type MOS output transistor, said first-conductivity-type MOS protection

transistor, said second-conductivity-type MOS output transistor, and said second-conductivity-type MOS protection transistor are of an SOI structure.

~~8~~ 23. (currently amended): The semiconductor apparatus according to claim ~~22~~<sup>7</sup>, comprising:

a second-conductivity-type  $\pm$  area connected to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor; and

a first-conductivity-type area connected to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor,

wherein the gate of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type  $\pm$  area to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor, and

wherein the gate of said second-conductivity-type MOS protection transistor is connected via said first-conductivity-type area to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~9~~ 24. (original): The semiconductor apparatus according to claim ~~21~~<sup>6</sup>, wherein the gates of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are connected by electrode wirings respectively to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor and to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~10~~ 25. (original): The semiconductor apparatus according to claim ~~21~~<sup>6</sup>, wherein the drains of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are formed closer to the output electrode than the drains of said first-

conductivity-type MOS output transistor and said second-conductivity-type MOS output transistor.

~~11~~ 26. (original): The semiconductor apparatus according to claim ~~10~~ 25, wherein said first-conductivity-type MOS output transistor, said first-conductivity-type MOS protection transistor, said second-conductivity-type MOS output transistor, and said second-conductivity-type MOS protection transistor are of an SOI structure.

~~12~~ 27. (currently amended): The semiconductor apparatus according to claim ~~11~~ 26, comprising:  
a second-conductivity-type  $\pm$  area connected to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor; and  
a first-conductivity-type area connected to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor,  
wherein the gate of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type  $\pm$  area to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor, and  
wherein the gate of said second-conductivity-type MOS protection transistor is connected via said first-conductivity-type area to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~13~~ 28. (original): The semiconductor apparatus according to claim ~~10~~ 25, wherein the gates of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are connected by electrode wirings respectively to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor and to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~14~~  
29. (original): The semiconductor apparatus according to claim ~~28~~<sup>13</sup>, wherein said first-conductivity-type MOS output transistor, said first-conductivity-type MOS protection transistor, said second-conductivity-type MOS output transistor, and said second-conductivity-type MOS protection transistor are of an SOI structure.

~~15~~  
30. (currently amended): The semiconductor apparatus according to claim ~~29~~<sup>14</sup>, comprising:

[[a]] wherein the second-conductivity-type  $\pm$  area is connected to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor; and

a first-conductivity-type area connected to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor,

wherein the gate of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type  $\pm$  area to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor, and

wherein the gate of said second-conductivity-type MOS protection transistor is connected via said first-conductivity-type area to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~30~~  
31. (previously presented): The semiconductor apparatus according to claim ~~32~~<sup>16</sup>, wherein the gate electrode of said first-conductivity-type MOS protection transistor is directly connected by the electrode wiring to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.



16  
~~22.~~ (currently amended): A semiconductor apparatus comprising:

an output electrode from which an output signal of the semiconductor apparatus is output;

a first-conductivity-type MOS output transistor respectively including a drain electrode connected to the output electrode, a source electrode connected to a ground voltage terminal, a gate electrode connected to a signal line, and a second-conductivity-type layer located under the gate electrode, wherein the first-conductivity-type MOS output transistor transmits the output signal of the semiconductor apparatus to the output electrode responsive to a signal on the signal line;

a first-conductivity-type MOS protection transistor respectively including a drain electrode connected to the output electrode, a source electrode connected to the ground voltage terminal, and a gate electrode connected to the ground voltage terminal; and

a metallic wiring member which connects the second-conductivity-type layer of the first-conductivity-type MOS output transistor to the gate electrode of the first-conductivity-type MOS protection transistor;

wherein said first-conductivity-type MOS output transistor further includes a second-conductivity-type + area which is formed in said second-conductivity-type layer and substantially surrounds said drain electrode and said source electrode.